

Appendix B: Table and Figure Format

Table 1.1. Electrical properties of recyclic growth epi-layer with added Ga solution and GaAs source.

Sample	Source (repetitions)	$\mu_{RT}^{a)}$ ($\text{cm}^2\text{V}^{-1}.\text{s}^{-1}$)	$\mu_{77\text{K}}^{b)}$ ($\text{cm}^2\text{V}^{-1}.\text{s}^{-1}$)	$n_{RT}^{a)}$ (cm^{-3})	$n_{77\text{K}}^{b)}$ (cm^{-3})
S1	A(1)	5600	4.01×10^4	3.90×10^{14}	4.99×10^{14}
S2	A(2)	4310	8.48×10^4	4.29×10^{13}	1.75×10^{14}
S3 ^{c)}	A(3)	5230	9.19×10^4	1.14×10^{13}	1.41×10^{14}
S4 ^{c)}	A(4)	5830	1.12×10^5	3.81×10^{13}	9.68×10^{13}
S5 ^{c)}	A(5)	7140	1.55×10^5	3.73×10^{12}	7.35×10^{13}

^{a)} Measured in dark.

^{b)} Measured under light illumination.

^{c)} These samples were used for the photoluminescence measurements.

Figure format Page

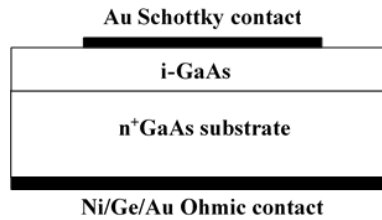


Fig. 1.1 Cross section of a Schottky diode used for capacitance-voltage measurement.

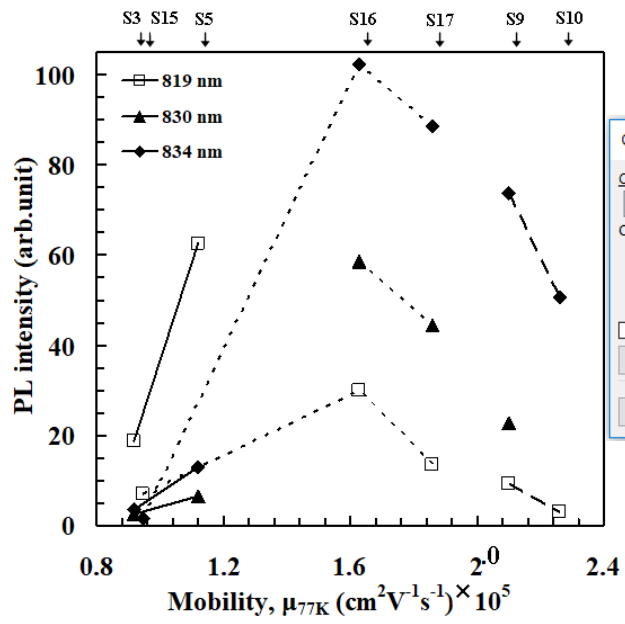


Fig. 2.1 PL intensity versus mobility at 77 K for samples from different lots at three different wavelengths. (Solid lines Lot A; thick broken lines Lot B; thin broken lines Lot D). Joined lines indicate the same lot.